

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 600V EMCON 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power module
- discrete components



Applications:

drives

Chip Type	V_R	I _F	Die Size	Package	
SIDC14D60C6	600V	50A	4.6 x 3.05 mm ²	sawn on foil	

MECHANICAL PARAMETER:

Raster size	4.6 x 3.05			
Area total / active	14.03 / 11.12			
Anode pad size	3.9 x 2.35			
Thickness	70	μm		
Wafer size	150	mm		
Flat position	180	deg		
Max. possible chips per wafer	1013 pcs			
Passivation frontside	Photoimide			
Anode metallization	3200 nm AlSiCu			
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding			
Die bond	electrically conductive glue or solder			
Wire bond	AI, ≤500μm			
Reject ink dot size	Ø 0.65mm; max 1.2mm			
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C			

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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by	1_		1)	
T_{jmax}	1 _F		·	Α
Maximum repetitive forward current	1		100	
limited by T _{jmax}	/FRM		100	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-40+175	°C

¹⁾ depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), T_{j} =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
raiailletei	Symbol	Conditions		min.	Тур.	max.	Onit
Reverse leakage current	I _R	V _R =600V	T _j =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	I _R =0.25mA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V _F	I _F =50A	<i>T_j</i> =25 °C	1.2	1.6	1.9	V

Dynamic Electrical Characteristics (verified by design/characterization), inductive load

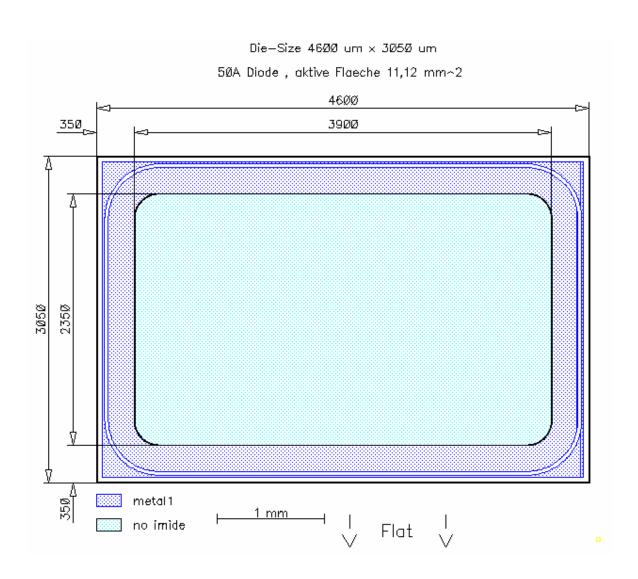
Parameter	Symbol	Conditions		Value 2)			Unit
raiailletei	Symbol	Condi	min.	Тур.	max.	Joint	
Peak reverse recovery		I _F =50A	$T_j = 25 ^{\circ}\text{C}$		69.0		
current	I _{RM}	di/dt=2800A/ms	$T_j = 125 ^{\circ}\text{C}$		76.0		Α
		$V_R=300V$ $V_{GE}=-15V$	$T_j = 150 ^{\circ}\mathrm{C}$		80.0		
Recovered charge	Qr	I _F =50A	$T_j = 25 ^{\circ}C$		1.90		
		di/dt=2800A/ms	$T_{i} = 125 ^{\circ}C$		3.40		μC
		$V_R=300V$ $V_{GE}=-15V$	$T_j = 150 ^{\circ}\text{C}$		3.95		
Reverse recovery energy	$E_{ m rec}$	I _F =50A	$T_j = 25 ^{\circ}\text{C}$		0.60		
		di/dt=2800A/ms	$T_{j} = 125 {}^{\circ}\text{C}$		0.95		mJ
	$V_R = 300V$ $V_{GE} = -15V$	$T_j = 150 ^{\circ}\mathrm{C}$		1.10			

²⁾ values also influenced by parasitic L- and C- in measurement and package.

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CHIP DRAWING:





This chip data sheet refers to the device data sheet Description: AQL 0,65 for visual inspection according to failure catalog Electrostatic Discharge Sensitive Device according to MIL-STD 883 Test-Normen Villach/Prüffeld

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